L # Hits DBs Time Stamp Type Search Text USPAT; 2002/01/07 1 BRS L1 145 438/142 EPO; 08:51 JPO USPAT; semiconductor adj side adj 2002/01/07 EPO; 2 BRS L2 wall adj fin 08:53 JPO USPAT; 2002/01/07 103 side adj wall adj fin EPO; 3 BRS L3 08:54 JPO USPAT; 2002/01/07 4 BRS L4 575 wall adj fin EPO; 08:54 JPO USPAT; 2002/01/07 10 5 BRS L5 / semiconductor adj fin EPO; 08:55 JPO USPAT; 2002/01/07 6 BRS L6 56541 fet EPO; 08:55 JPO USPAT; double adj gated adj field 2002/01/07 L7 L EPO; 7 BRS 08:56 adj effect adj transistor JPO USPAT; 2002/01/07 401 EPO; 8 BRS $\Gamma8$ SOI adj MOSFET 08:56 JPO USPAT; 2002/01/07 L9 | 33 9 BRS EPO; damascene adj gate 08:57 JPO USPAT; 2002/01/07 10 EPO: L10 103 3 and 4BRS 08:57 JPO USPAT; 2002/01/07 1 and 3 EPO; 11 BRS L11 0 08:58 JPO USPAT; 2002/01/07 L12, 26 1 and 6 12 BRS EPO; 08:58 JPO

	Туре	L #	Hits	Search Text	DBs	Time Stamp
13	BRS	L13	0	3 and 6		2002/01/07 08:58
14	BRS	L14	0	3 and 8	; H. P() *	2002/01/07 08:58
15	BRS	L15	146	6 and 8	USPAT; EPO; JPO	2002/01/07 08:58
16	BRS	L16	1	// 0. 47.		2002/01/07 08:59
17	BRS	L17	0	4 and 6 and 8	USPAT; EPO; JPO	2002/01/07 08:59

<u>L15</u>
-6,326,247
\$6,323,082
-6,303,479
-6,232,163
-6,159,778
-6063,686
* 5,981,318
\$ 5,780,329
* 5,713,328
A 5,736,437

5	47	<u> </u>	112
(-5,349,128	-6,333, 247	-6,323,103
	-5,273,921	-6,333,229	-6,284,637
		-6,329,756	#6,114, 195
		¥6 ,291,278	\$ \$ 950,076
		-6,271,132	5,944,970
		\$ 6,258,679	